

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,828,235 B2
DATED : December 7, 2004
INVENTOR(S) : Satoshi Takano

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 17.

Line 45, claim 9 should read as follows:

9. A substrate processing method, comprising
a first step of carrying a substrate into a preliminary chamber from an external part;

a second step of continuously supplying and exhausting an inert gas to and from said preliminary chamber at least from a time before opening a first gate between said preliminary chamber and a transfer chamber, after the substrate is carried into said preliminary chamber;

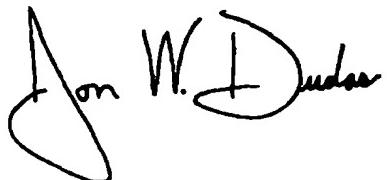
a third step of transferring said substrate to said transfer chamber from said preliminary chamber, in a state in which the inert gas is continuously supplied and exhausted to and from said preliminary chamber and said transfer chamber, after said first gate valve is opened;

a fourth step of transferring said substrate to a process chamber from said transfer chamber in a state in which the inert gas is continuously supplied and exhausted to and from said transfer chamber and said process chamber, after a second gate valve between said transfer chamber and said process chamber is opened; and

a fifth step of subjecting said substrate to predetermine processing in said process chamber.

Signed and Sealed this

Fourteenth Day of June, 2005



JON W. DUDAS
Director of the United States Patent and Trademark Office